

UNISONIC TECHNOLOGIES CO., LTD

MJE13007-P

Preliminary

## NPN SILICON TRANSISTOR

# NPN BIPOLAR POWER TRANSISTOR FOR SWITCHING POWER SUPPLY APPLICATIONS

## DESCRIPTION

The UTC **MJE13007-P** is designed for high-voltage, high-speed power switching inductive circuits where fall time is critical. It is particularly suited for 115 and 220 V switch mode applications.

## FEATURES

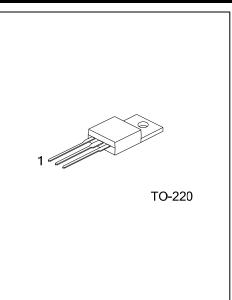
\* V<sub>CEO(SUS)</sub> 400V

\* 700V Blocking Capability

### ORDERING INFORMATION

Ordering	Deekege	Pin Assignment			Deaking		
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE13007L-P-TA3-T	MJE13007G-P-TA3-T	TO-220	В	С	Е	Tube	
Note: Pin Assignment: B: Base	C: Collector E: Emitter						

MJE13007L-P- <u>TA3-T</u> (1)Packing Type (2)Package Type (3)Lead Free	



## ■ ABSOLUTE MAXIMUM RATING

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Sustaining Voltage		V <sub>CEO</sub>	400	V
Collector-Emitter Breakdown Voltage		V <sub>CBO</sub>	700	V
Emitter-Base Voltage		V <sub>EBO</sub>	9.0	V
Collector Current	Continuous	Ιc	8.0	А
	Peak (1)	I <sub>CM</sub>	16	А
During and	Continuous	Ι <sub>Β</sub>	4.0	А
Base Current	Peak (1)	I <sub>BM</sub>	8.0	А
	Continuous	Ι <sub>Ε</sub>	12	А
Emitter Current	Peak (1)	I <sub>EM</sub>	I <sub>EM</sub> 24	
Power Dissipation ( $T_c = 25^{\circ}C$ )		PD	80	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T <sub>STG</sub>	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ <sub>JA</sub>	62.5	°C/W	
Junction to Case	θ <sub>JC</sub>	1.56	°C/W	

Note: 1. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle  $\leq 10\%$ .

Measurement made with thermocouple contacting the bottom insulated mounting surface of the package (in a location beneath the die), the device mounted on a heatsink with thermal grease applied at a mounting torque of 6 to 8•lbs.

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL		MIN	TVD	MAX	UNIT	
					IVIAA		
Collector-Emitter Sustaining Voltage	V <sub>CEO(SUS)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	400			V	
Collector Cutoff Current	Ісво	V <sub>CES</sub> =700V			0.1	mA	
	ICBO	V <sub>CES</sub> =700V, T <sub>C</sub> =125°C	$I_B=0$ 400 $OV$ 0 $OV, T_C=125^{\circ}C$ 1 $I, I_C=0$ 10 $V_{CE}=5.0V$ 8.0 $V_{CE}=5.0V$ 5.0 $I_B=0.4A$ 1 $I_B=1.0A$ 2 $I_B=2.0A$ 3 $I_B=1.0A, T_C=100^{\circ}C$ 3 $I_B=1.0A, T_C=100^{\circ}C$ 1 $I_B=1.0A, T_C=100^{\circ}C$ 1 $I_B=1.0A, T_C=100^{\circ}C$ 1 $I_B=1.0A, T_C=100^{\circ}C$ 14 $I_B=1.0A, T_C=10V, f=1.0 MHz$ 4.0       14 $I_L=0, f=0.1MHz$ 80       0.025       0	1.0	mA		
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =9.0V, I <sub>C</sub> =0			100	μA	
DC Current Gain	h <sub>FE1</sub>	I <sub>C</sub> =2.0A, V <sub>CE</sub> =5.0V	8.0		40		
	h <sub>FE2</sub>	I <sub>C</sub> =5.0A, V <sub>CE</sub> =5.0V	5.0		30		
	V <sub>CE(SAT)</sub>	I <sub>C</sub> =2.0A, I <sub>B</sub> =0.4A			1.0	V	
Collector Emitter Seturation Voltage		I <sub>C</sub> =5.0A, I <sub>B</sub> =1.0A			2.0	V	
Collector-Emitter Saturation Voltage		I <sub>C</sub> =8.0A, I <sub>B</sub> =2.0A			3.0	V	
		I <sub>C</sub> =5.0A, I <sub>B</sub> =1.0A, T <sub>C</sub> =100°C			3.0	V	
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	I <sub>C</sub> =2.0A, I <sub>B</sub> =0.4A			1.2	V	
		I <sub>C</sub> =5.0A, I <sub>B</sub> =1.0A			1.6	V	
		I <sub>C</sub> =5.0A, I <sub>B</sub> =1.0A, T <sub>C</sub> =100°C			1.5	V	
Current-Gain-Bandwidth Product	f⊤	I <sub>C</sub> =500mA, V <sub>CE</sub> =10V, f=1.0 MHz	4.0	14		MHz	
Output Capacitance	C <sub>OB</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=0.1MHz		80		pF	
RESISTIVE LOAD (TABLE 1)							
Delay Time	t <sub>D</sub>			0.025	0.1	μs	
Rise Time	t <sub>R</sub>	$V_{\rm CC}$ =125V, I <sub>C</sub> =5.0A,		0.5	1.5	μs	
Storage Time	ts	I <sub>B1</sub> =I <sub>B2</sub> =1.0A, t <sub>P</sub> =25µs, Duty Cycle≤1.0%		1.8	4.0	μs	
Fall Time	t⊧			0.23	0.7	μs	

Note: Pulse Test: Pulse Width≤300µs, Duty Cycle≤2.0%



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## TYPICAL THERMAL RESPONSE

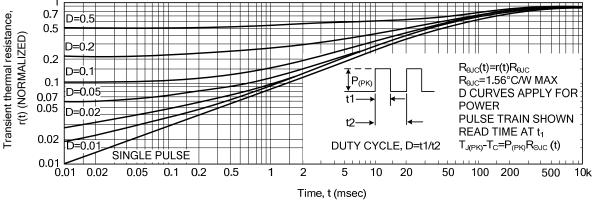


Fig. 1 Typical Thermal Response

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_{C}-V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Fig. 7 is based on  $T_C = 25^{\circ}C$ ;  $T_{J(PK)}$  is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be debated when  $T_C \ge 25^{\circ}C$ . Second breakdown limitations do not debate the same as thermal limitations. Allowable current at the voltages shown on Fig. 7 may be found at any case temperature by using the appropriate curve on Fig. 9.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

Use of reverse biased safe operating area data (Fig. 8) is discussed in the applications information section.



#### **TYPICAL THERMAL RESPONSE(Cont.)**

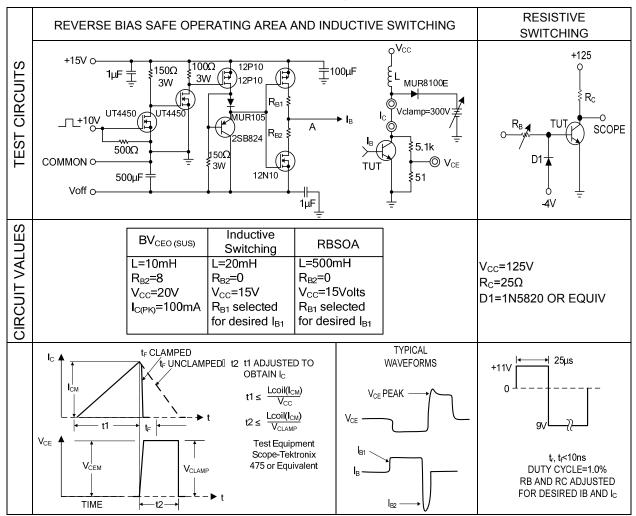


 Table 1. Test Conditions for Dynamic Performance

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